



PATENT  
740756-2222

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/699,466

Filed: October 31, 2000

For: METHOD FOR FABRICATING A  
SEMICONDUCTOR DEVICE

Art Unit: 2813

Examiner: T. NGUYEN

RECEIVED  
DEC 31 2001  
TC 2800: AIL ROOM

AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

December 26, 2001

Dear Sir:

In response to the Examiner's non-Final Office Action mailed September 26, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please add the following new claims 26-34 as follows:

- 26. A method for manufacturing a thin film transistor, comprising the steps of:
- forming a semiconductor film on an insulating surface;
  - crystallizing said semiconductor film;
  - forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;
  - irradiating laser light to said semiconductor island; and
  - forming an insulating film on said semiconductor island.

12/27/2001 MGBREM1 00000035 09699466

01 FC:102  
02 FC:103

252.00 OP  
162.00 OP

NVA209566.2